

Application Serial No. 11,29,694
Reply to Office Action of January 21, 2005

PATENT
Docket: CU-3477

Amendments To The Claims

The listing of claims presented below will replace all prior versions, and listings, of claims in the application.

Listing of claims:

1. **(currently amended)** A method for fabricating a capacitor in a semiconductor device, the method comprising the steps of:
forming an interlayer insulating film on a semiconductor substrate, which includes a first contact hole exposing a ~~certain~~ portion of the substrate;
forming a storage node plug filling the first contact hole;
forming a first insulating film, a first silicon nitride film, and a second insulating film sequentially above the substrate inclusive of the storage node plug;
forming a second contact hole that exposes the storage node plug by removing the second insulating film, the first silicon nitride film, and the first insulating film partly;
forming a recessed portion at side surfaces of the second contact hole and below the silicon nitride film by wet-etching the first insulating film remained in the second contact hole;
forming a storage node electrode of the capacitor, which is connected to the storage node plug, by filling the second contact hole inclusive of the recessed portion;
removing the remained second insulating film; and
forming a dielectric film on the storage node electrode; and
forming a plate electrode ~~sequentially on the entire surface of the storage node electrode on the dielectric film and the silicon nitride film.~~ structure.

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2. (currently amended) The method as claimed in claim 1, further comprising a step of forming a second silicon nitride film at least on the interlayer insulating film above the resultant substrate inclusive of the first contact hole, before forming the first insulating film 180.
3. (original) The method as claimed in claim 1, wherein the first insulating film has an etching rate faster than that of the first silicon nitride film.
4. (original) The method as claimed in claim 3, wherein the first insulating film comprises a BSPG film.
5. (original) The method as claimed in claim 1, wherein the second insulating film is formed to a thickness of 10000 ~ 20000Å.
6. (original) The method as claimed in claim 1, wherein the second insulating film comprises a PSG film.
7. (original) The method as claimed in claim 1, wherein the recessed portion of the storage node electrode has a broader width than that of any other portion of the storage node electrode.